

at least one pixel electrode provided on said interlayer insulating layer,

wherein said thin-film transistor comprises:

a semiconductor layer comprising a source region, a drain region, and a channel formation region between said source region and said drain region; and

a gate electrode provided adjacent to said channel formation region with a gate insulating film interposed therebetween.

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46 48. The device of claim 45 wherein said resinous substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide.

47 49. The device of claim 45 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, and 2-ethylhexyl ester of acrylic acid.

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48 50. The device of claim 45 wherein said interlayer insulating layer comprises polyimide.

49 51. The device of claim 45 wherein said semiconductor layer comprises silicon.

50 52. The device of claim 45 wherein said semiconductor device is a liquid crystal display device.

51 53. A semiconductor device comprising:
a resinous substrate having an uneven surface;
a resinous layer provided on said uneven surface of said resinous substrate and having a planarized surface; and

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a thin-film transistor provided on said planarized surface of said resinous layer;

an interlayer insulating layer comprising a resinous material provided over said thin-film transistor; and

at least one pixel electrode provided on said interlayer insulating layer,

wherein said thin-film transistor comprises:

a semiconductor layer comprising a source region, a drain region, and a channel formation region between said source region and said drain region; and

a gate electrode provided over said channel formation region with a gate insulating film interposed therebetween.

52 54. The device of claim 53 wherein said resinous substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide.

53 55. The device of claim 53 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, and 2-ethylhexyl ester of acrylic acid.

54 56. The device of claim 53 wherein said interlayer insulating layer comprises polyimide.

55 57. The device of claim 53 wherein said semiconductor layer comprises silicon.

56 58. The device of claim 53 wherein said semiconductor device is a liquid crystal display device.

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57 59. A semiconductor device comprising:

- a resinous substrate having an uneven surface, wherein said resinous substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide;
- a resinous layer provided on said uneven surface of said resinous substrate and having a planarized surface;
- a thin film transistor provided on said planarized surface of said resinous layer; and
- an interlayer insulating layer comprising resinous material provided over said thin film transistor,

wherein said thin film transistor comprises:

- a semiconductor layer comprising a source region, a drain region, and a channel formation region provided between said source region and said drain region; and
- a gate electrode provided adjacent to said channel formation region with a gate insulating film interposed therebetween.

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58 60. The device of claim ⁵⁷59 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, and 2-ethylhexyl ester of acrylic acid.

57 61. The device of claim ⁵⁷59 wherein said interlayer insulating layer comprises polyimide.

64 62. The device of claim ⁵⁷59 wherein said semiconductor layer comprises silicon.

61 63. The device of claim ⁵⁷59 wherein said semiconductor device is a liquid crystal display device.

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64. A semiconductor device comprising:

a resinous substrate having an uneven surface, wherein said resinous substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide;

a resinous layer provided on said uneven surface of said resinous substrate and having a planarized surface;

a thin film transistor provided on said planarized surface of said resinous layer; and

an interlayer insulating layer comprising resinous material provided over said thin film transistor,

wherein said thin film transistor comprises:

a semiconductor layer comprising a source region, a drain region, and a channel formation region provided between said source region and said drain region; and

a gate electrode provided over said channel formation region with a gate insulating film interposed therebetween.

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65. The device of claim 64 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, and 2-ethylhexyl ester of acrylic acid.

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66. The device of claim 64 wherein said interlayer insulating layer comprises polyimide.

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67. The device of claim 64 wherein said semiconductor layer comprises silicon.

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68. The device of claim 64 wherein said semiconductor device is a liquid crystal display device.

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68 69. A semiconductor device comprising:

- a resinous substrate having an uneven surface, wherein said resinous substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide;
- a resinous layer provided on said uneven surface of said resinous substrate and having a planarized surface;
- a thin film transistor provided on said planarized surface of said resinous layer; and
- an interlayer insulating layer comprising resinous material provided over said thin film transistor,
- at least one pixel electrode provided on said interlayer insulating layer,

wherein said thin film transistor comprises:

- a semiconductor layer comprising a source region, a drain region, and a channel formation region provided between said source region and said drain region; and
- a gate electrode provided over said channel formation region with a gate insulating film interposed therebetween.

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68 70. The device of claim *67* wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, and 2-ethylhexyl ester of acrylic acid.

68 71. The device of claim *67* wherein said interlayer insulating layer comprises polyimide.

70 72. The device of claim *69* wherein said semiconductor layer comprises silicon.

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8) 73. The device of claim 69 wherein said semiconductor device is a liquid crystal display device.--
